

WHAT IS CLAIMED IS:

1. A side-emission type semiconductor light-emitting device, comprising:  
a substrate formed with an electrode;  
an LED chip bonded onto said electrode; and  
5 a transparent or translucent resin with which said LED chip is molded, wherein  
said transparent or translucent resin has a light-emitting surface formed by a  
roughened surface being perpendicular to said substrate.
2. A side-emission type semiconductor light-emitting device according to claim 1,  
wherein said light-emitting surface is formed by dicing.
- 10 3. A manufacturing method of a side-emission type semiconductor light-emitting  
device, comprising the following steps of:  
(a) mounting two reflectors having openings opposed with each other on a  
substrate mounted with an LED chip;  
(b) injecting a transparent or translucent resin at an opposing portion of said  
15 openings; and  
(c) dicing said transparent or translucent resin being hardened and said substrate at  
said opposing portion.
4. A side-emission type semiconductor light-emitting device, comprising:  
a substrate formed with an electrode;  
20 an LED chip bonded onto said substrate;  
a transparent or translucent resin with which said LED chip is molded; and  
a reflector which reflects a light emitted from said LED chip, wherein  
said transparent or translucent resin has a convex portion, and said reflector has a  
concave portion to be fitted into said convex portion.
- 25 5. A side-emission type semiconductor light-emitting device according to claim 4,

wherein said concave portion is a throughhole having a diameter which becomes larger from one main surface to other main surface of said reflector.

5 6. A side-emission type semiconductor light-emitting device according to claim 5, wherein said one main surface is a surface brought into contact with said transparent or translucent resin, and said other main surface is a surface exposed to outside.

7. A side-emission type semiconductor light-emitting device according to any one of claims 4 to 6, wherein said LED chip has a bonding wire extending from a top surface, and said concave portion is formed directly above said LED chip.

10 8. A manufacturing method of a side-emission type semiconductor light-emitting device, comprising the following steps of:

(a) mounting a reflector formed with a concave portion on a substrate;

(b) removing an organic matter adhering to a surface, including an inner surface of said concave portion, of said reflector; and

15 (c) injecting a transparent or translucent resin between said reflector and said substrate up to said concave portion.

9. A manufacturing method of a side-emission type semiconductor light-emitting device according to claim 8, wherein said reflector is subjected to UV cleaning in the step (b).

20 10. A side-emission type semiconductor light-emitting device, comprising:  
a substrate formed with an electrode; and  
an LED chip which is bonded onto said electrode by a bonding paste, wherein said LED chip has a transparent or translucent base and a light-emitting layer formed thereon, and is mounted on a position deviated from an application position of  
25 said bonding paste to a light emitting surface side.

11. A side-emission type semiconductor light-emitting device according to claim 10, wherein said electrode includes an application area having a center deviated from a mounted position of said LED chip to an opposite direction of said light-emitting surface.

5 12. A side-emission type semiconductor light-emitting device according to claim 11, wherein said electrode further includes an auxiliary area formed closer to said light-emitting surface side than said application area and a narrow connecting portion connecting said application area and said auxiliary area.

10 13. A side-emission type semiconductor light-emitting device according to claim 11 or 12, wherein a center of said application area is deviated from a center of said substrate to said opposite direction.

**BEST AVAILABLE COPY**